

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	250	semiconductor adj slab	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	2	1 with (buried adj layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	2	1 same (buried adj layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	3	1 with trench	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	15548	buried adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	361464	"257"/\$.ccls. or "438"/\$.ccls	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	8697	5 and 6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	2323	7 and trench	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	1489	7 and (trench with isolation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB